

Figure 4; shows a CTSe thin film the XRD pattern of a thin CTSe film obtained by through sequential deposition of thin films of CuSe and SnSe, with using a preparation routine like as one that plotted in Fig. 3 and with evaporated masses of Cu and Sn of 0.01 and 0.07 g, respectively. The Figure 4 also showed shows the XRD patterns for films of CuSe and SnSe films. These are were compared with the CTSe diffractogram my in order to get obtain with a greater degree of accuracy the reflections corresponding to secondary phases in the thin CTSe films with a greater degree of accuracy.

Comment [A1]: The simple present tense is used when referring to Figures/Tables present in text.

Cu_2SnSe_3 thin films were grown with using a method based on sequential evaporation of thin films of CuSe, and SnSe in a two two stage process. Characterization done performed by XRD gave evidence of the proved the formation of a compound formation containing predominantly the Cu_2SnSe_3 phase; however, the sequence with in which the binary precursors are evaporated and the preparation parameters, more significantly affects the phase as well as the structural, optical, and electrical transportation properties of the thin CTSe films. Moreover Optical characterization performed by spectral transmittance measurements revealed that the CTSe films have low transmittance and also poor crystallographic quality, probably associated to structural and native defects, indicating that further studies must be done to improve CTSe films properties. Furthermore, The the results revealed that characterize of the Cu_2SnSe_3 films is could be characterized done to get obtain p-type conductivity and with an energy band gap (E_g) of around somewhat 1.6 eV also.

Comment [A2]: Choosing the right technical words to convey meaning eases readability and understanding and maintains technical accuracy.

Temperature-dependent Conductivity conductivity measurements on temperature dependence revealed that the conductivities of the CTSe films were is predominantly affected with by

Comment [A3]: To create an easy flow of ideas, transition words such as however, therefore, moreover, etc. can be used. This usage enhances coherence of ideas in the paragraph and the manuscript on the whole.



the free carrier transport in states of the valence band. In high temperatures ranges ($T > 550$ K), the increase of σ could be attributed to an the increase of in the carrier density ies coming originating from deep acceptor impurities, whereas the change of σ observed in the low temperatures range ($T < 350$ K) can be attributed to a changes of in the carrier density of carrier coming originating from shallow acceptor impurities associated to with secondary phases.

SAMPLE

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